

10664440_CLS
Most Frequently Occurring Classifications of Patents Returned
From A Search of 10664440 on March 17, 2004

Original Classifications

14 250/310
5 324/751
4 250/491.1
4 250/492.2
2 250/309
2 250/398

Cross-Reference Classifications

13 250/397
8 250/310
7 250/307
7 250/492.2
6 250/311
5 250/306
4 250/396R
3 250/309
2 250/305
2 250/396ML
2 257/E21.295
2 257/E21.586
2 324/71.3
2 427/586
2 430/296

Combined Classifications

22 250/310
14 250/397
11 250/492.2
8 250/307
7 250/311
5 250/306
5 250/309
5 250/491.1
5 324/751
4 250/396R
3 250/305
2 219/121.35
2 250/396ML
2 250/398
2 257/E21.295
2 257/E21.586
2 324/71.3
2 427/586

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2 430/296

10664440_CLSTITLES

Titles of Most Frequently Occurring Classifications of Patents Returned

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22	250/310	(14 OR, 8 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/310	.Electron probe type
14	250/397	(1 OR, 13 XR)
	Class 250 :	RADIANT ENERGY
	250/396R	WITH CHARGED PARTICLE BEAM DEFLECTION OR FOCUSING
	250/397	.With detector
11	250/492.2	(4 OR, 7 XR)
	Class 250 :	RADIANT ENERGY
	250/492.1	IRRADIATION OF OBJECTS OR MATERIAL
	250/492.2	.Irradiation of semiconductor devices
8	250/307	(1 OR, 7 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/307	.Methods
7	250/311	(1 OR, 6 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/311	.Electron microscope type
5	250/306	(0 OR, 5 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
5	250/309	(2 OR, 3 XR)
	Class 250 :	RADIANT ENERGY
	250/306	INSPECTION OF SOLIDS OR LIQUIDS BY CHARGED PARTICLES
	250/309	.Positive ion probe or microscope type
5	250/491.1	(4 OR, 1 XR)
	Class 250 :	RADIANT ENERGY
	250/491.1	MEANS TO ALIGN OR POSITION AN OBJECT RELATIVE

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TO A SOURCE OR DETECTOR

5 324/751 (5 OR, 0 XR)
Class 324 : ELECTRICITY: MEASURING AND TESTING
324/500 FAULT DETECTING IN ELECTRIC CIRCUITS AND OF
ELECTRIC COMPONENTS
324/537 .Of individual circuit component or element
324/750 ..System sensing fields adjacent device under
test (DUT)
324/751 ...Using electron beam probe

4 250/396R (0 OR, 4 XR)
Class 250 : RADIANT ENERGY
250/396R WITH CHARGED PARTICLE BEAM DEFLECTION OR
FOCUSSING

3 250/305 (1 OR, 2 XR)
Class 250 : RADIANT ENERGY
250/305 ELECTRON ENERGY ANALYSIS

2 219/121.35 (1 OR, 1 XR)
Class 219 : ELECTRIC HEATING
219/50 METAL HEATING (E.G., RESISTANCE HEATING)
219/121.11 .By arc
219/121.12 ..Using electron beam
219/121.35 ...Methods

2 250/396ML (0 OR, 2 XR)
Class 250 : RADIANT ENERGY
250/396R WITH CHARGED PARTICLE BEAM DEFLECTION OR
FOCUSSING
250/396ML .Magnetic lens

2 250/398 (2 OR, 0 XR)
Class 250 : RADIANT ENERGY
250/396R WITH CHARGED PARTICLE BEAM DEFLECTION OR
FOCUSSING
250/398 .With target means

2 257/E21.295 (0 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE

OR TREATMENT OF SEMICONDUCTOR OR SOL
ID-STATE DEVICES OR OF
PARTS THEREOF (EPO)
257/E21.002 .Manufacture or treatment of semiconductor
device (EPO)

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257/E21.04 ..Device having at least one potential-jump
 barrier or surface barrier, e.g., PN j
 unction, depletion
 layer, carrier concentration layer (EP
 O)

257/E21.085 ...Device having semiconductor body comprising
 Group IV elements or Group III-V compou
 nds with or without
 impurities, e.g., doping materials (EPO
)

257/E21.211Treatment of semiconductor body using
 process other than deposition of semicon
 ductor material on
 a substrate, diffusion or alloying of im
 purity material, or
 radiation treatment (EPO)

257/E21.214To change their surface-physical
 characteristics or shape, e.g., etching,
 polishing, cutting
 (EPO)

257/E21.294Deposition/post-treatment of
 noninsulating, e.g., conductive - or resis
 tive - layers on
 insulating layers (EPO)

257/E21.295Deposition of layer comprising metal,
 e.g., metal, alloys, metal compounds (EPO)

2 257/E21.586 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E21.531 ...For electrical parameters, e.g.,
 resistance, deep-levels, CV, diffusio
 ns by electrical means
 (EPO)

257/E21.532 .Manufacture or treatment of devices
 consisting of plurality of solid-state
 components formed in
 or on common substrate or of parts the
 reof; manufacture of
 integrated circuit devices or of parts
 thereof (EPO)

257/E21.536 ..Manufacture of specific parts of devices
 (EPO)

257/E21.575 ...Interconnections, comprising conductors and
 dielectrics, for carrying current betwee
 n separate
 components within device (EPO)

257/E21.576Characterized by formation and post

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treatment of dielectrics, e.g., planariz
ing (EPO)
257/E21.585Filling of holes, grooves, vias or
trenches with conductive material (EPO)
257/E21.586By selective deposition of conductive
material in vias, e.g., selective chemical
vapor deposition
on semiconductor material, plating (EPO)

2 324/71.3 (0 OR, 2 XR)
Class 324 : ELECTRICITY: MEASURING AND TESTING
324/71.1 DETERMINING NONELECTRIC PROPERTIES BY MEASURIN
G
ELECTRIC PROPERTIES
324/71.3 .Beam of atomic particles

2 427/586 (0 OR, 2 XR)
Class 427 : COATING PROCESSES
427/457 DIRECT APPLICATION OF ELECTRICAL, MAGNETIC,
WAVE, OR PARTICULATE ENERGY
427/585 .Chemical vapor deposition (e.g., electron bea
m
or heating using IR, inductance, resistanc
e, etc.)
427/586 ..Pyrolytic use of laser or focused light
(e.g., IR, UV lasers to heat, etc.)

2 430/296 (0 OR, 2 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
430/269 IMAGING AFFECTING PHYSICAL PROPERTY OF
RADIATION SENSITIVE MATERIAL, OR PRODUCING
NONPLANAR OR
PRINTING SURFACE - PROCESS, COMPOSITION, O
R PRODUCT
430/296 .Electron beam imaging